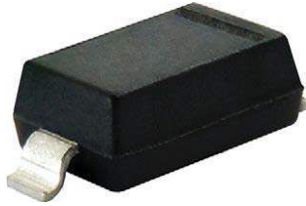




Small Signal Switching Diodes, High Voltage



FEATURES

- Silicon epitaxial planar diodes
- For general purpose
- AEC-Q101 qualified available (part number on request)
- Base P/N-G3 - green, commercial grade
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



DESIGN SUPPORT TOOLS

[click logo to get started](#)



MECHANICAL DATA

Case: SOD-123

Weight: approx. 9.4 mg

Packaging codes / options:

18/10K per 13" reel (8 mm tape), 10K/box

08/3K per 7" reel (8 mm tape), 15K/box

PARTS TABLE					
PART	TYPE DIFFERENTIATION	ORDERING CODE	TYPE MARKING	CIRCUIT CONFIGURATION	REMARKS
BAV19W-G	V _R = 100 V	BAV19W-G3-08 or BAV19W-G3-18	AS	Single	Tape and reel
BAV20W-G	V _R = 150 V	BAV20W-G3-08 or BAV20W-G3-18	AT	Single	Tape and reel
BAV21W-G	V _R = 200 V	BAV21W-G3-08 or BAV21W-G3-18	AU	Single	Tape and reel

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	PART	SYMBOL	VALUE	UNIT
Continuous reverse voltage		BAV19W-G	V _R	100	V
		BAV20W-G	V _R	150	V
		BAV21W-G	V _R	200	V
Repetitive peak reverse voltage		BAV19W-G	V _R RM	120	V
		BAV20W-G	V _R RM	200	V
		BAV21W-G	V _R RM	250	V
DC forward current ⁽¹⁾			I _F	250	mA
Rectified current (average) half wave rectification with resist. load ⁽¹⁾			I _{F(AV)}	200	mA
Repetitive peak forward current ⁽¹⁾	f ≥ 50 Hz		I _{FRM}	625	mA
Surge forward current	t < 1 s		I _{FSM}	1	A
Power dissipation ⁽¹⁾			P _{tot}	410	mW

THERMAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance junction to ambient air ⁽¹⁾		R _{thJA}	375	K/W
Junction temperature ⁽¹⁾		T _j	150	°C
Storage temperature range ⁽¹⁾		T _{stg}	-65 to +150	°C
Operating temperature range		T _{op}	-55 to +150	°C

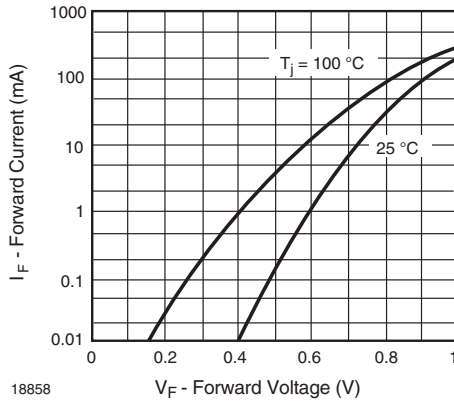
Note

⁽¹⁾ Valid provided that leads are kept at ambient temperature



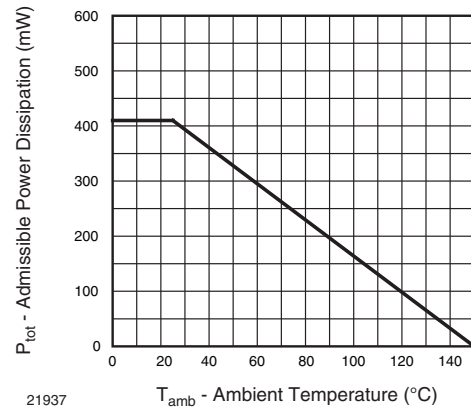
ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA		V _F			1	V
	I _F = 200 mA		V _F			1250	mV
Leakage current	V _R = 100 V	BAV19W-G	I _R			100	nA
	V _R = 100 V, T _j = 100 °C	BAV19W-G	I _R			15	μA
	V _R = 150 V	BAV20W-G	I _R			100	nA
	V _R = 150 V, T _j = 100 °C	BAV20W-G	I _R			15	μA
	V _R = 200 V	BAV21W-G	I _R			100	nA
	V _R = 200 V, T _j = 100 °C	BAV21W-G	I _R			15	μA
Dynamic forward resistance	I _F = 10 mA		r _f		5		Ω
Diode capacitance	V _R = 0, f = 1 MHz		C _D		1.5		pF
Reverse recovery time	I _F = 30 mA, I _R = 30 mA, i _R = 3 mA, R _L = 100 Ω		t _{rr}			50	ns

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)



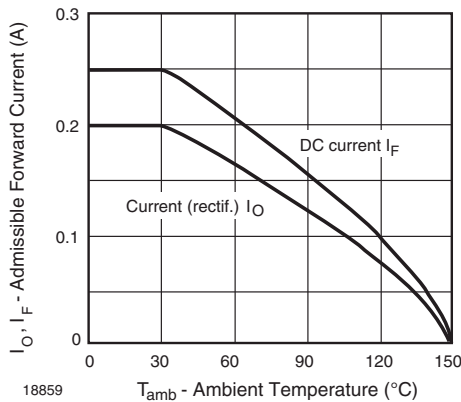
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Fig. 1 - Forward Current vs. Forward Voltage



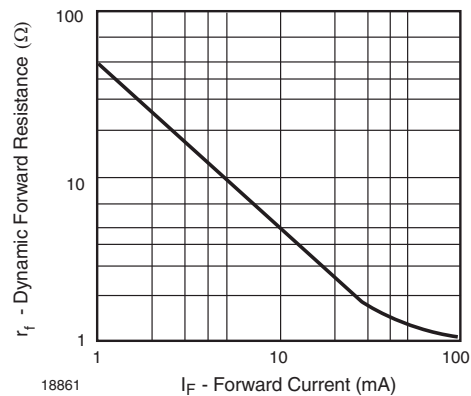
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Fig. 3 - Admissible Power Dissipation vs. Ambient Temperature



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Fig. 2 - Admissible Forward Current vs. Ambient Temperature



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Fig. 4 - Dynamic Forward Resistance vs. Forward Current

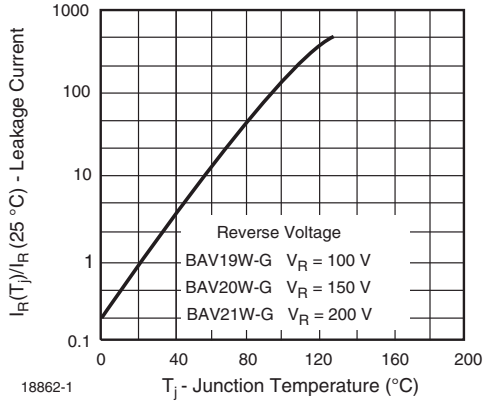


Fig. 5 - Leakage Current vs. Junction Temperature

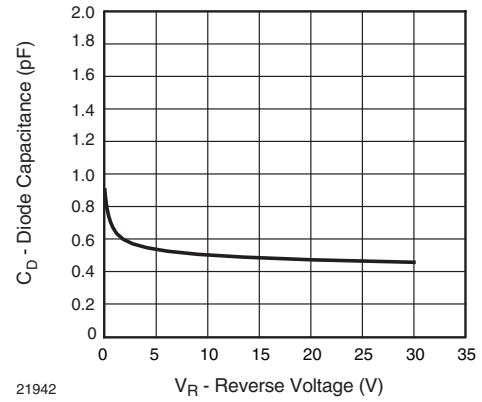


Fig. 6 - Diodes Capacitance vs. Reverse Voltage

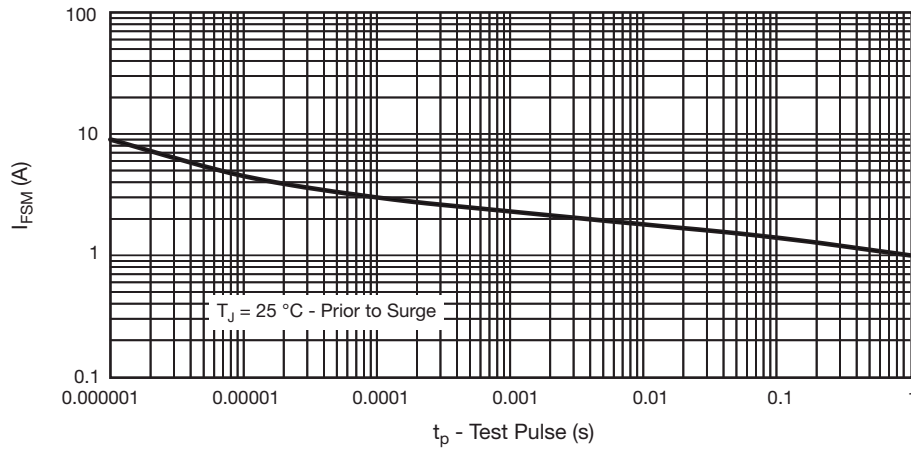
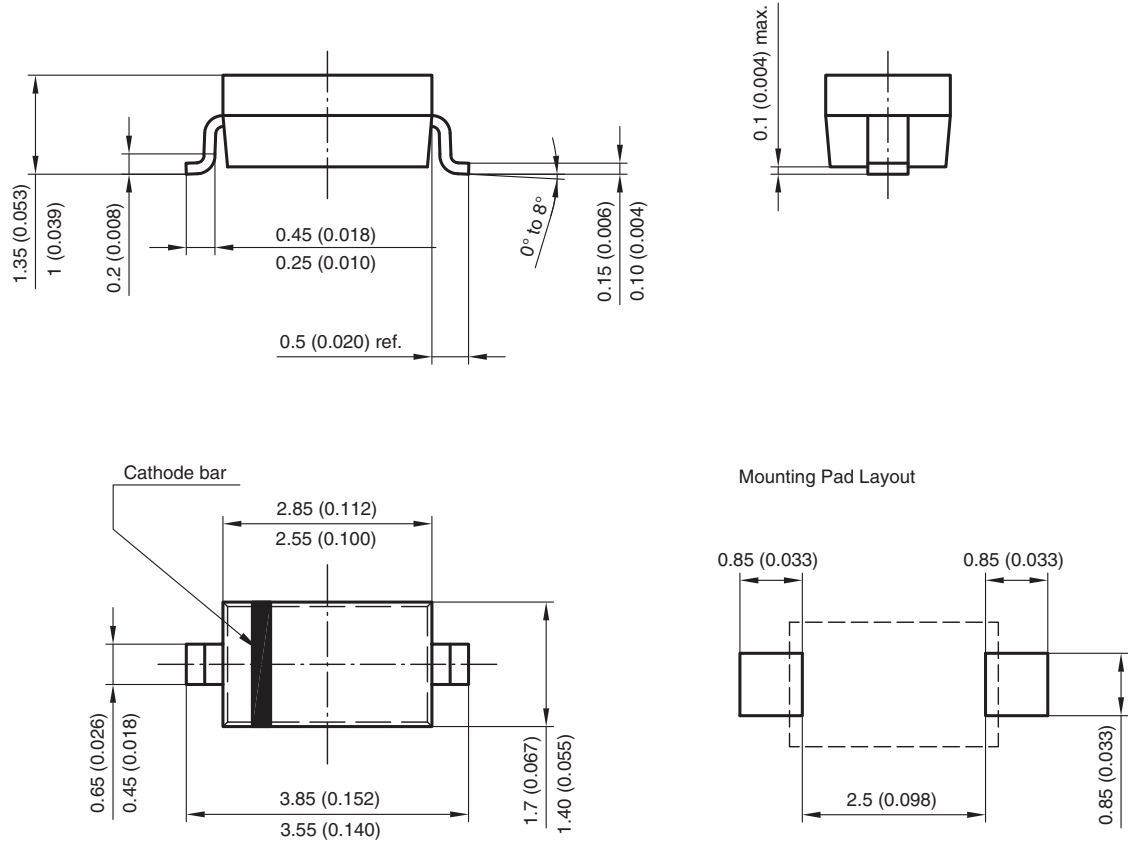


Fig. 7 - Non-Repetitive Peak Forward Current vs. Pulse Duration
Maximum Admissible Values of Square Pulses



PACKAGE DIMENSIONS in millimeters (inches): SOD-123



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